

A cross-sectional view of a semiconductor device 100. The device consists of a substrate 102 with a top layer 106. A patterned layer 104 is on the substrate, with openings 103. A layer 118 is on top of 104, with openings 120. A layer 122 is on top of 118, with openings 122. A layer 108 is on top of 122, with openings 108. A layer 116 is on top of 108, with openings 116.

A cross-sectional view of a semiconductor device 100. The device features a substrate 102 with a base layer 104. A first conductive layer 106 is formed on the substrate, with a second conductive layer 108 on top of it. A third conductive layer 110 is formed on the second conductive layer. A fourth conductive layer 112 is formed on the third conductive layer. A fifth conductive layer 114 is formed on the fourth conductive layer. A sixth conductive layer 116 is formed on the fifth conductive layer. A seventh conductive layer 118 is formed on the sixth conductive layer. A eighth conductive layer 120 is formed on the seventh conductive layer. A ninth conductive layer 122 is formed on the eighth conductive layer. A tenth conductive layer 124 is formed on the ninth conductive layer. A eleventh conductive layer 125 is formed on the tenth conductive layer. The device includes various openings and vias, such as 103, 108, 112, 114, 116, 118, 120, 122, 124, and 125, which are filled with conductive material. The device is labeled 100 in the top right corner.

Fig. 1B

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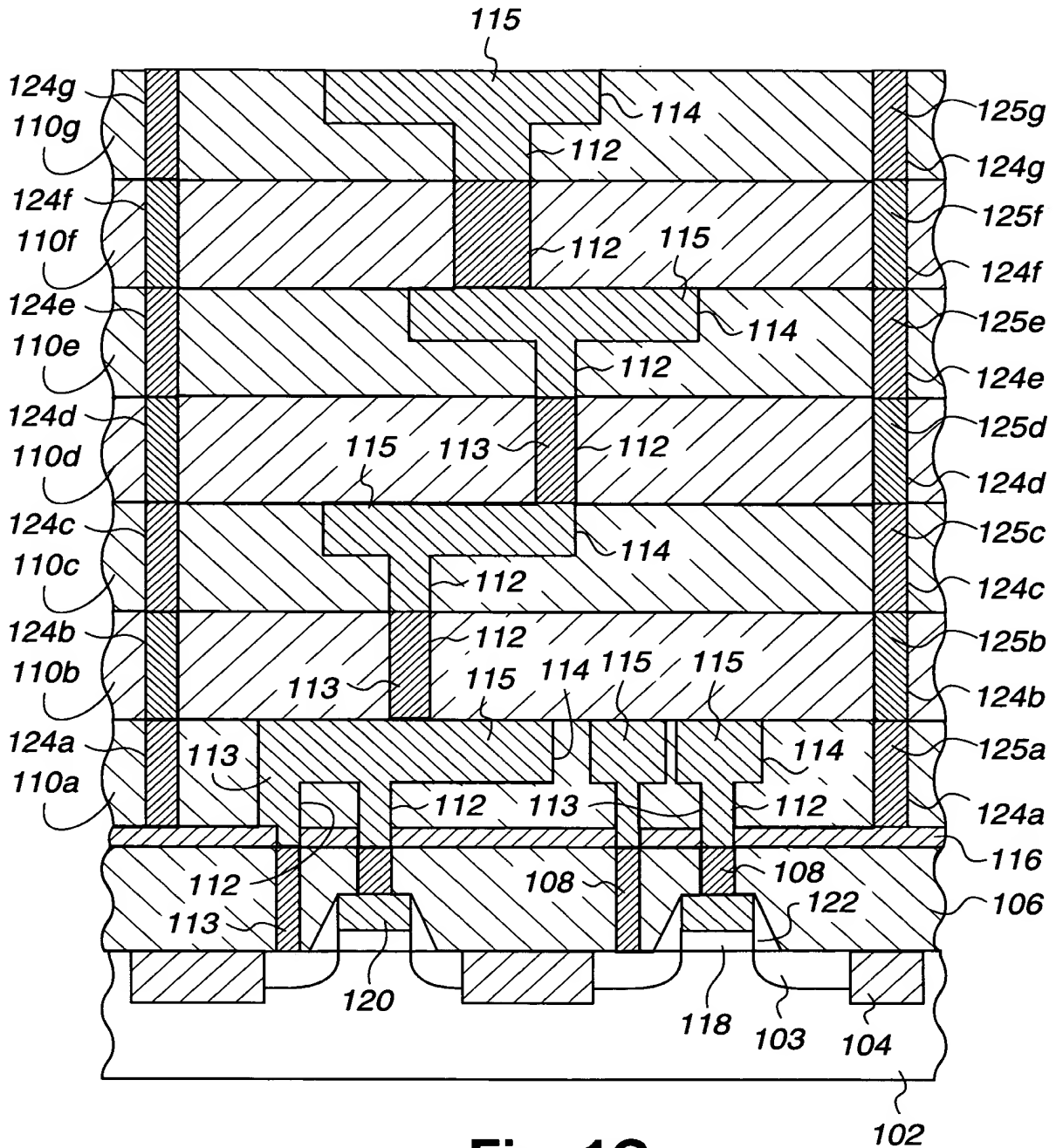
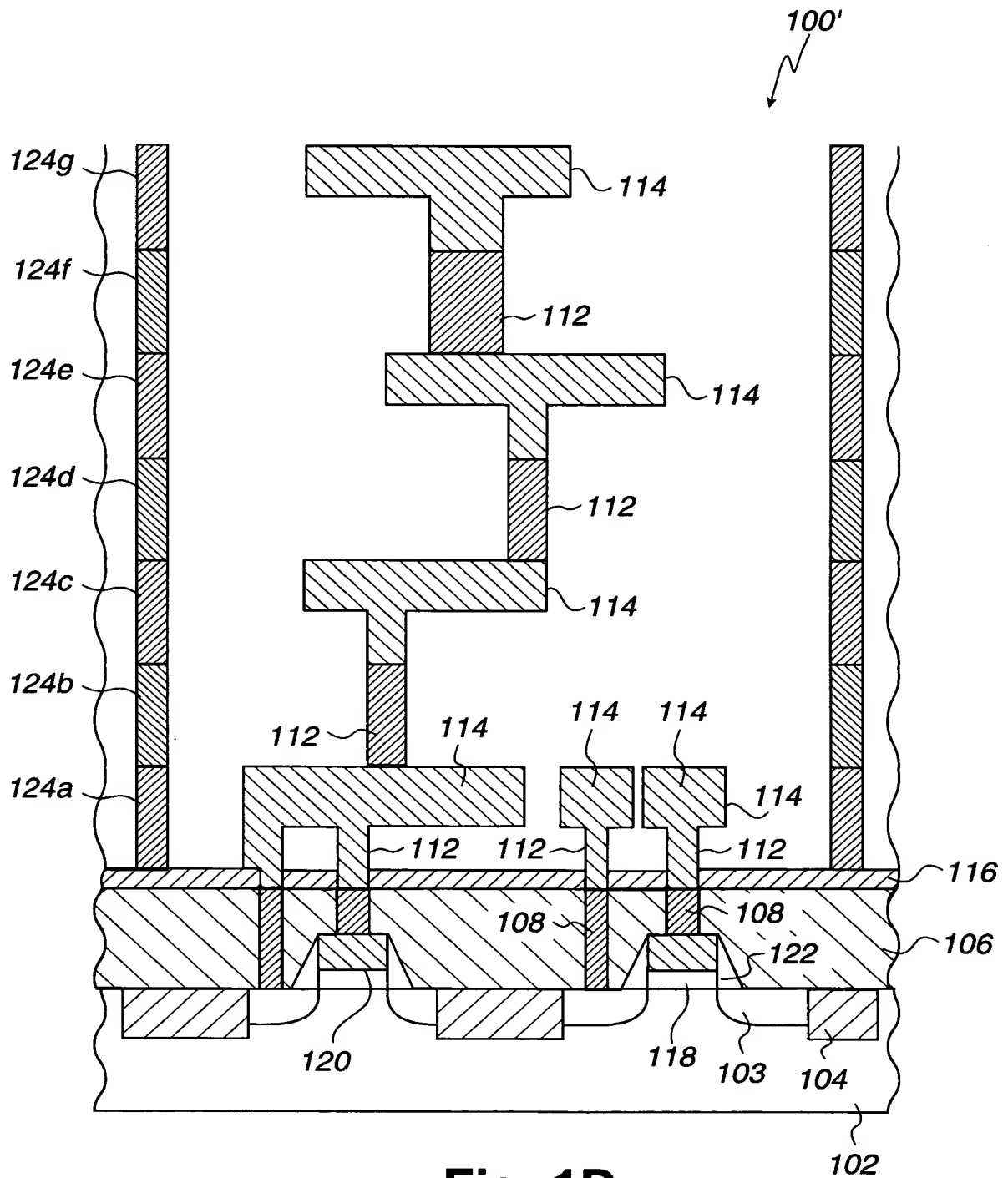


Fig. 1C

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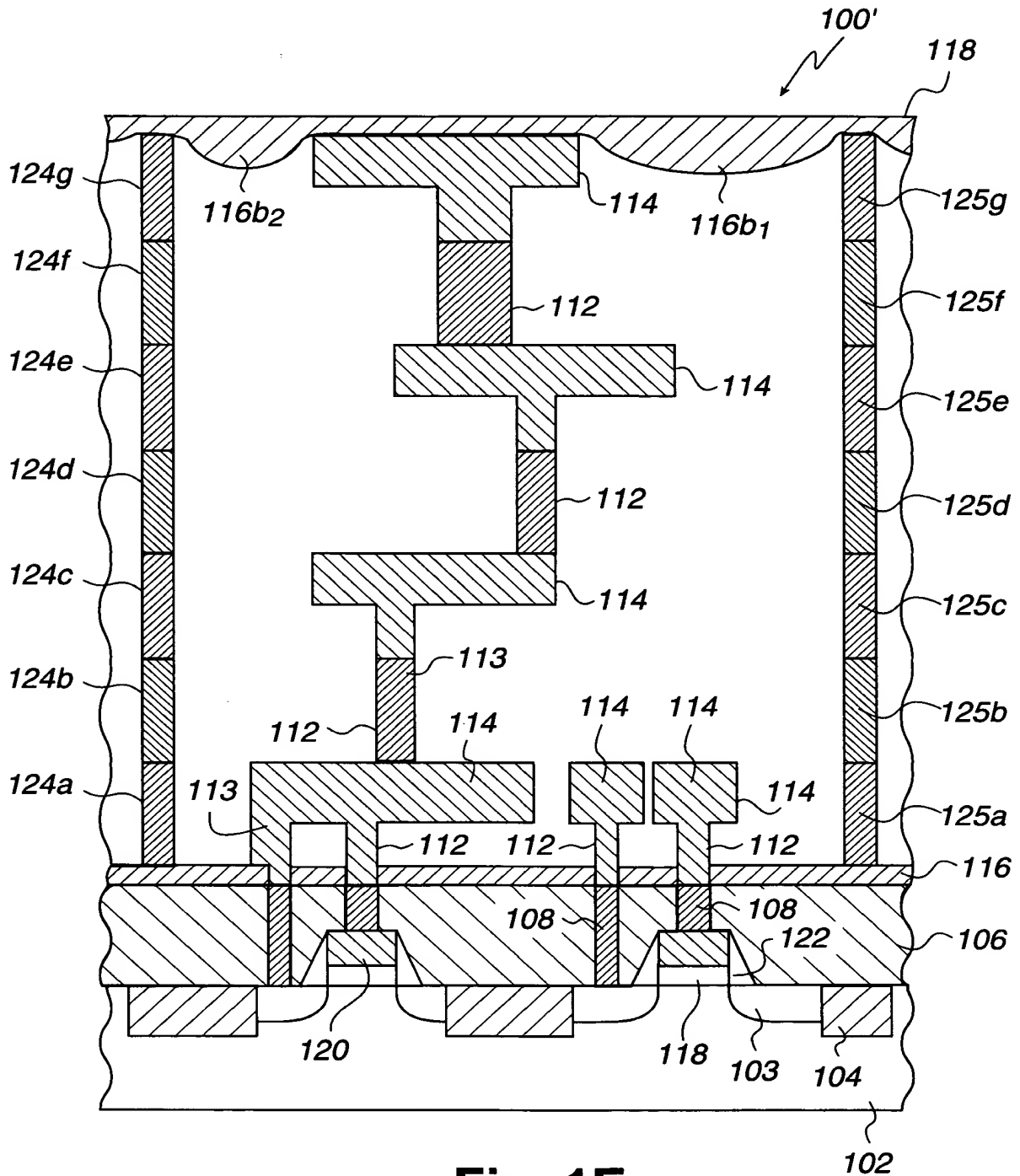
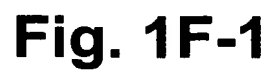


Fig. 1E



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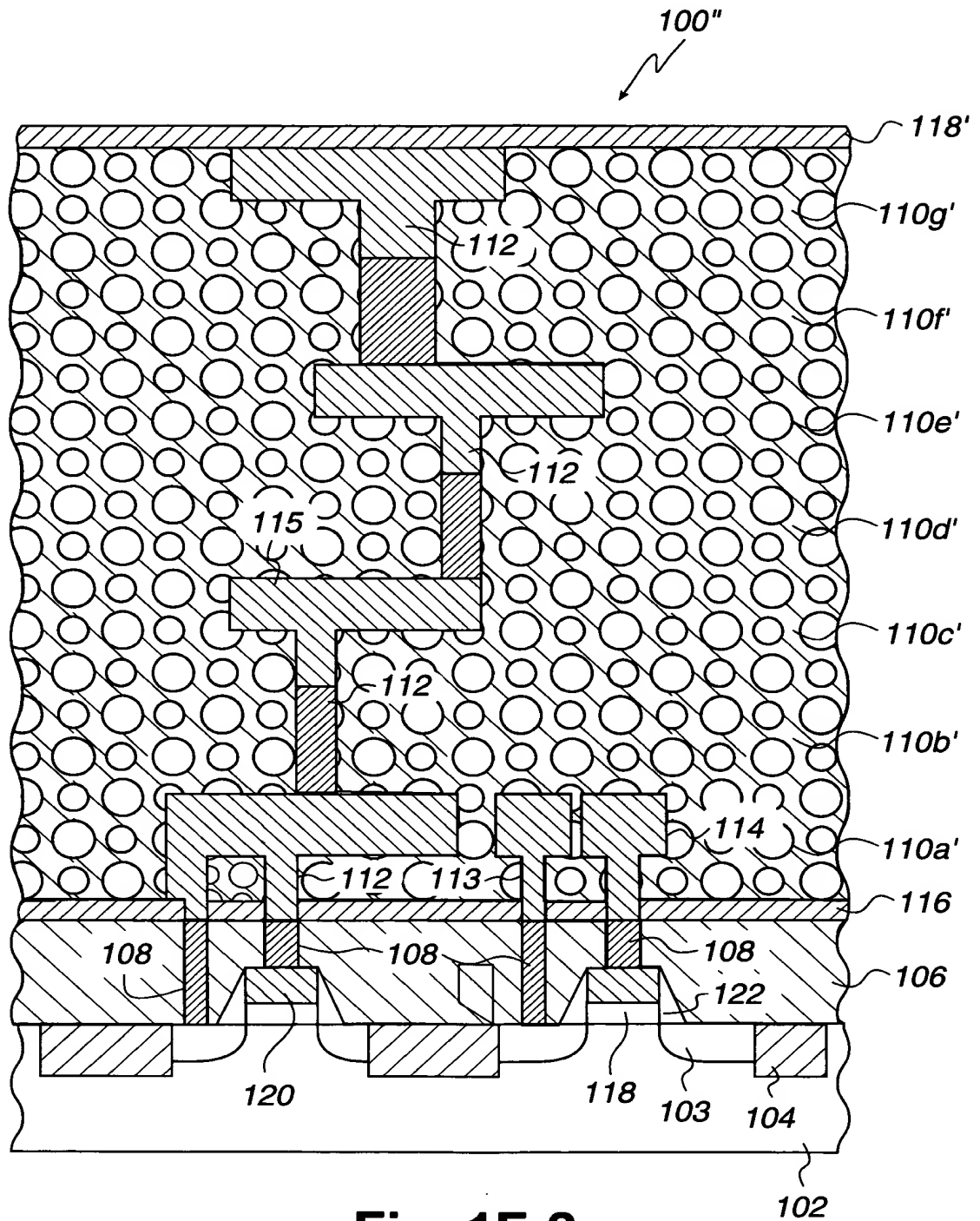


Fig. 1F-2

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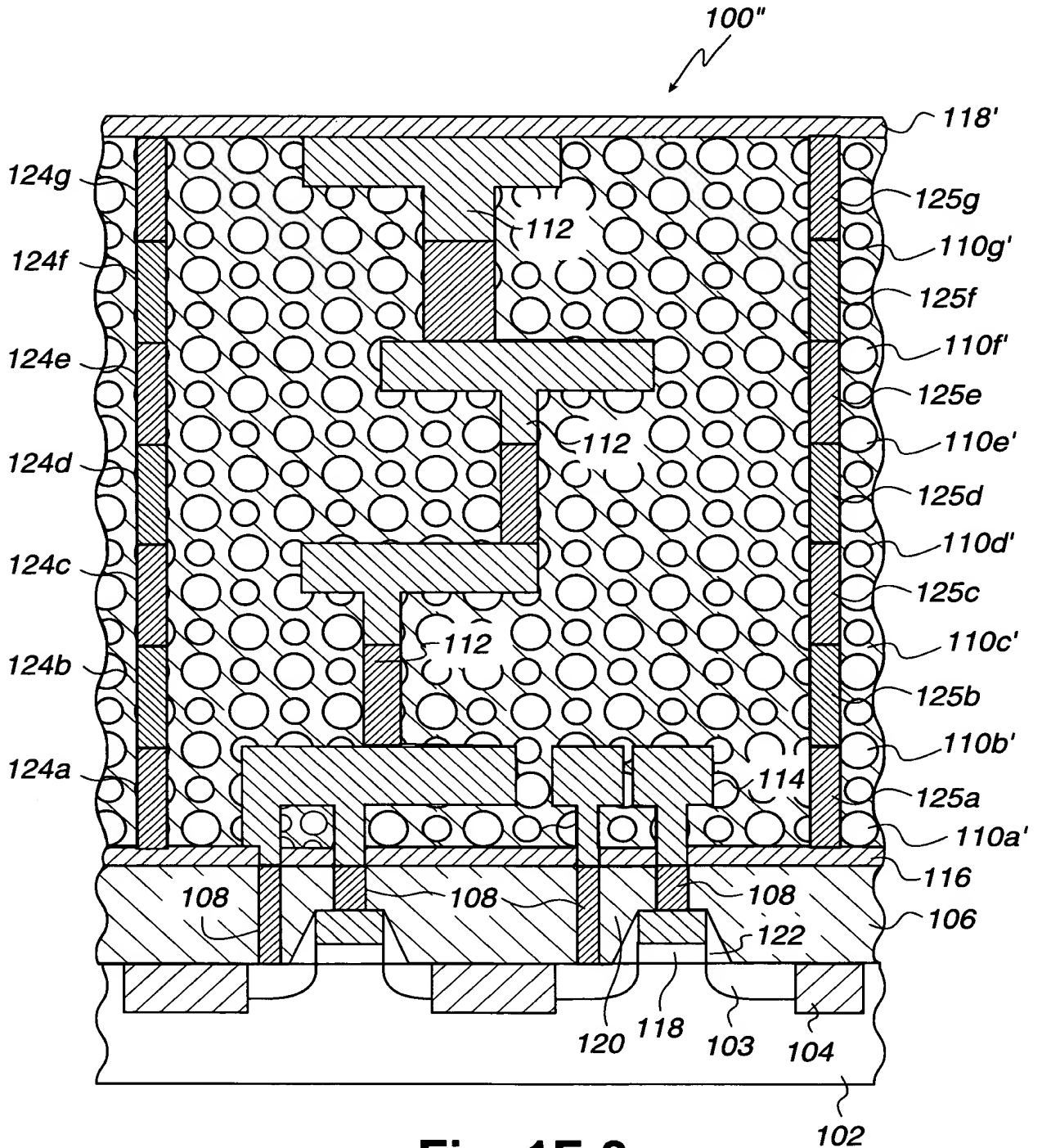
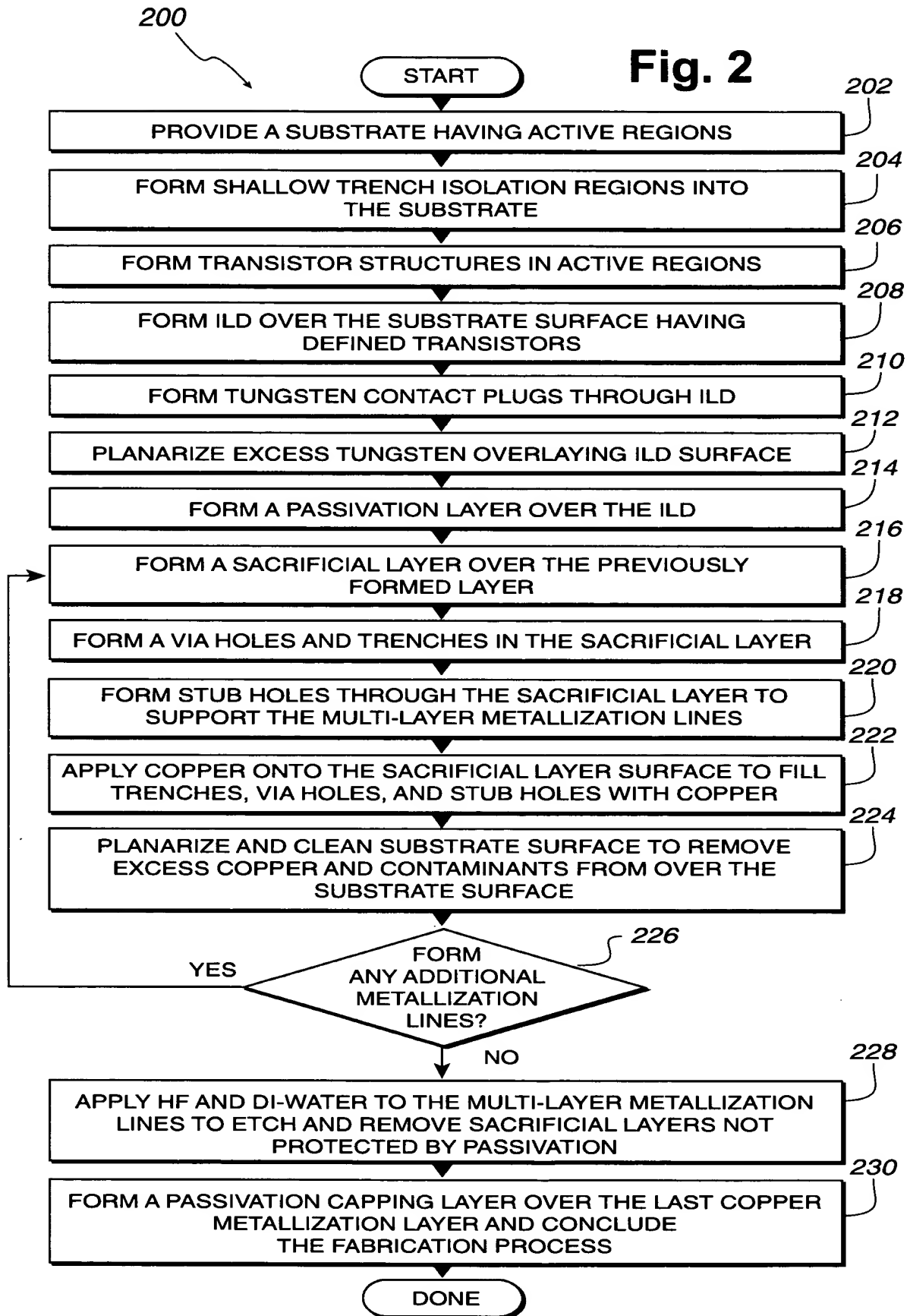


Fig. 1F-3

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Fig. 2



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Fig. 3

